NTHC5513

Power MOSFET

20 V, +3.9 A / −3.0 A, Complementary ChipFET™

Features

- Complementary N−Channel and P−Channel MOSFET
- Small Size, 40% Smaller than TSOP−6 Package
- Leadless SMD Package Featuring Complementary Pair
- ChipFET Package Provides Great Thermal Characteristics Similar to Larger Packages
- Low $R_{DS(on)}$ in a ChipFET Package for High Efficiency Performance
- Low Profile (< 1.10 mm) Allows Placement in Extremely Thin Environments Such as Portable Electronics
- Pb−Free Package is Available

Applications

- Load Switch Applications Requiring Level Shift
- DC−DC Conversion Circuits
- Drive Small Brushless DC Motors
- Designed for Power Management Applications in Portable, Battery Powered Products

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	20	V
Gate−to−Source Voltage			V_{GS}	±12	V
Continuous Drain Current (Note 1)	N−Ch Steady State	T_A = 25°C	I_D	2.9	A
		T_A = 85°C		2.1	
	t ≤ 5	T_A = 25°C		3.9	
	P−Ch Steady State	T_A = 25°C	I_D	−2.2	A
		T_A = 85°C		−1.6	
	t ≤ 5	T_A = 25°C		−3.0	
Pulsed Drain Current (Note 1)	N−Ch	t = 10 μs	I_{DM}	12	A
	P−Ch	t = 10 μs		−9.0	
Power Dissipation (Note 1)	Steady State	T_A = 25°C	P_D	1.1	W
	t ≤ 5	T_A = 25°C		2.1	
Operating Junction and Storage Temperature			T_J, T_{STG}	−55 to 150	°C
Lead Temperature for Soldering Purposes (1/8” from case for 10 seconds)			T_L	260	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Surface Mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

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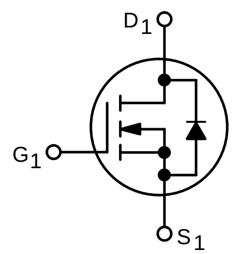
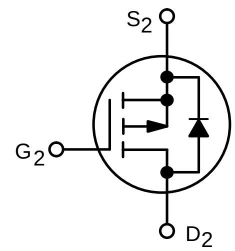
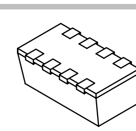
$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D MAX
N−Channel 20 V	60 mΩ @ 4.5 V	3.9 A
	80 mΩ @ 2.5 V	
P−Channel −20 V	130 mΩ @ −4.5 V	−3.0 A
	200 mΩ @ −2.5 V	



N−Channel MOSFET

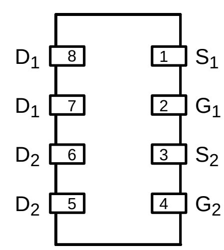


P−Channel MOSFET

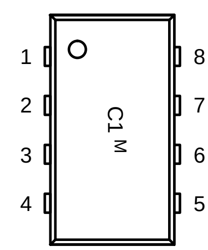


ChipFET
CASE 1206A
STYLE 2

PIN CONNECTIONS



MARKING DIAGRAM



C1 = Specific Device Code
M = Month Code

ORDERING INFORMATION

Device	Package	Shipping†
NTHC5513T1	ChipFET	3000/Tape & Reel
NTHC5513T1G	ChipFET (Pb−Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

THERMAL RESISTANCE RATINGS

Parameter			Symbol	Max	Unit
Junction−to−Ambient (Note 1)	Steady State	T_A = 25°C	$R_{\theta JA}$	110	°C/W
	t ≤ 5			60	

2. Surface Mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	N/P	Test Conditions		Min	Typ	Max	Unit
OFF CHARACTERISTICS (Note 3)								
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	N	V_{GS} = 0 V	I_D = 250 μA	20			V
		P		I_D = −250 μA	−20			
Zero Gate Voltage Drain Current	I_{DSS}	N	V_{GS} = 0 V, V_{DS} = 16 V				1.0	μA
		P	V_{GS} = 0 V, V_{DS} = −16 V				−1.0	
		N	V_{GS} = 0 V, V_{DS} = 16 V, T_J = 85 °C				5	
		P	V_{GS} = 0 V, V_{DS} = −16 V, T_J = 85 °C				−5	
Gate−to−Source Leakage Current	I_{GSS}		V_{DS} = 0 V, V_{GS} = ±12 V				±100	nA
ON CHARACTERISTICS (Note 3)								
Gate Threshold Voltage	$V_{GS(TH)}$	N	V_{GS} = V_{DS}	I_D = 250 μA	0.6		1.2	V
		P		I_D = −250 μA	−0.6		−1.2	
Drain−to−Source On Resistance	R_{DS}(on)	N	V_{GS} = 4.5 V , I_D = 2.9 A			0.058	0.080	Ω
		P	V_{GS} = −4.5 V , I_D = −2.2 A			0.130	0.155	
		N	V_{GS} = 2.5 V , I_D = 2.3 A			0.077	0.115	
		P	V_{GS} = −2.5 V, I_D = −1.7 A			0.200	0.240	
Forward Transconductance	g_{FS}	N	V_{DS} = 10 V, I_D = 2.9A			6.0		S
		P	V_{DS} = −10 V , I_D = −2.2 A			6.0		
CHARGES AND CAPACITANCES								
Input Capacitance	C_{ISS}	N	f = 1 MHz, V_{GS} = 0 V	V_{DS} = 10 V		180		pF
		P		V_{DS} = −10 V		185		
Output Capacitance	C_{OSS}	N		V_{DS} = 10 V		80		
		P		V_{DS} = −10 V		95		
Reverse Transfer Capacitance	C_{RSS}	N		V_{DS} = 10 V		25		
		P		V_{DS} = −10 V		30		
Total Gate Charge	$Q_{G(TOT)}$	N	V_{GS} = 4.5 V, V_{DS} = 10 V, I_D = 2.9 A			2.6	4.0	nC
		P	V_{GS} = −4.5 V, V_{DS} = −10 V, I_D = −2.2 A			3.0	6.0	
Gate−to−Source Gate Charge	Q_{GS}	N	V_{GS} = 4.5 V, V_{DS} = 10 V, I_D = 2.9 A			0.6		
		P	V_{GS} = −4.5 V, V_{DS} = −10 V, I_D = −2.2 A			0.5		
Gate−to−Drain “Miller” Charge	Q_{GD}	N	V_{GS} = 4.5 V, V_{DS} = 10 V, I_D = 2.9 A			0.7		
		P	V_{GS} = −4.5 V, V_{DS} = −10 V, I_D = −2.2 A			0.9		

3. Pulse Test: Pulse Width ≤ 250 μs, Duty Cycle ≤ 2%.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	N/P	Test Conditions		Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS (Note 4)								
Turn−On Delay Time	$t_{d(ON)}$	N	V_{DD} = 16 V, V_{GS} = 4.5 V, I_D = 2.9 A, R_G = 2.5 Ω			5.0	10	ns
Rise Time	t_r					9.0	18	
Turn−Off Delay Time	$t_{d(OFF)}$					10	20	
Fall Time	t_f					3.0	6.0	
Turn−On Delay Time	$t_{d(ON)}$	P	V_{DD} = −16 V, V_{GS} = −4.5 V, I_D = −2.2 A, R_G = 2.5 Ω			7.0	12	
Rise Time	t_r					13	25	
Turn−Off Delay Time	$t_{d(OFF)}$					33	50	
Fall Time	t_f					27	40	
DRAIN−SOURCE DIODE CHARACTERISTICS								
Forward Diode Voltage (Note 5)	V_{SD}	N	V_{GS} = 0 V	I_S = 2.6 A		0.8	1.15	V
		P		I_S = −2.1 A		−0.8	−1.15	
Reverse Recovery Time (Note 4)	t_{RR}	N	V_{GS} = 0 V, dI_S / dt = 100 A/μs	I_S = 1.5 A		12.5		ns
		P		I_S = −1.5 A		32		
Charge Time	t_a	N		I_S = 1.5 A		9.0		
		P		I_S = −1.5 A		10		
Discharge Time	t_b	N		I_S = 1.5 A		3.5		
		P		I_S = −1.5 A		22		
Reverse Recovery Charge	Q_{RR}	N		I_S = 1.5 A		6.0		nC
		P		I_S = −1.5 A		15		

4. Switching characteristics are independent of operating junction temperatures.
5. Pulse Test: Pulse Width ≤ 250 μs, Duty Cycle ≤ 2%.

TYPICAL N−CHANNEL PERFORMANCE CURVES

(T_J = 25°C unless otherwise noted)

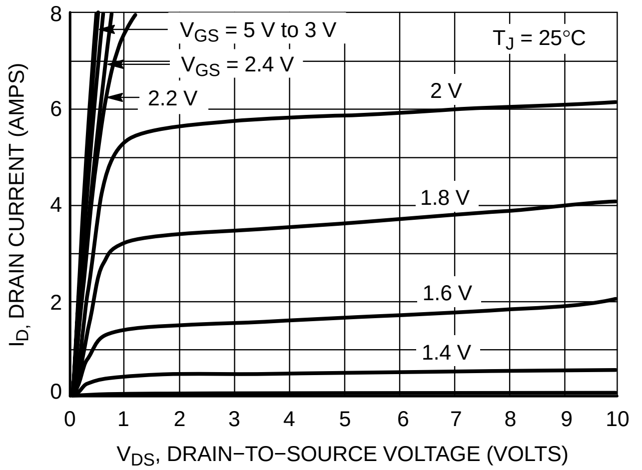


Figure 1. On−Region Characteristics

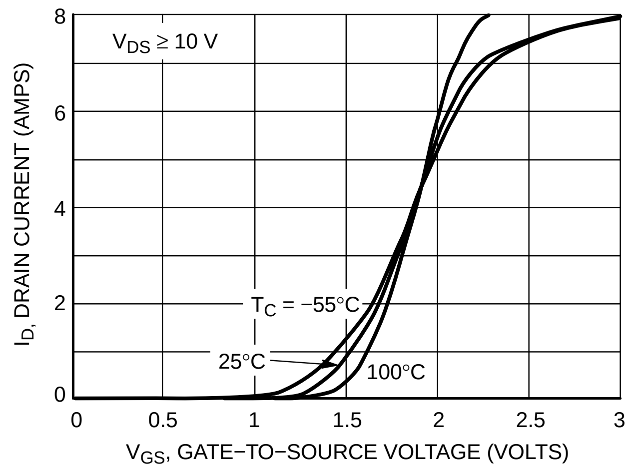


Figure 2. Transfer Characteristics

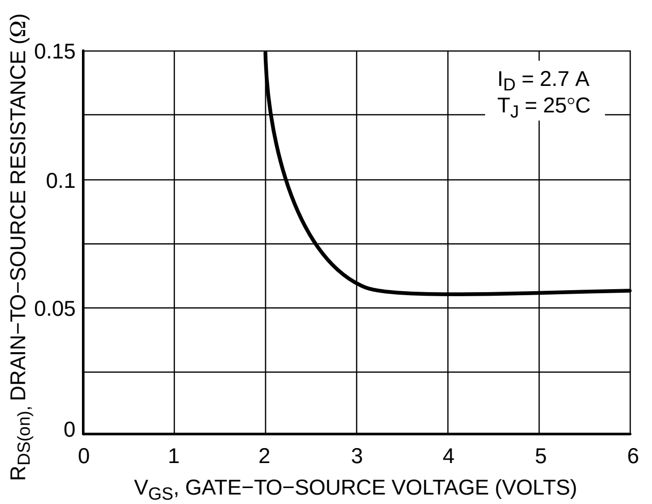


Figure 3. On−Resistance vs. Gate−to−Source Voltage

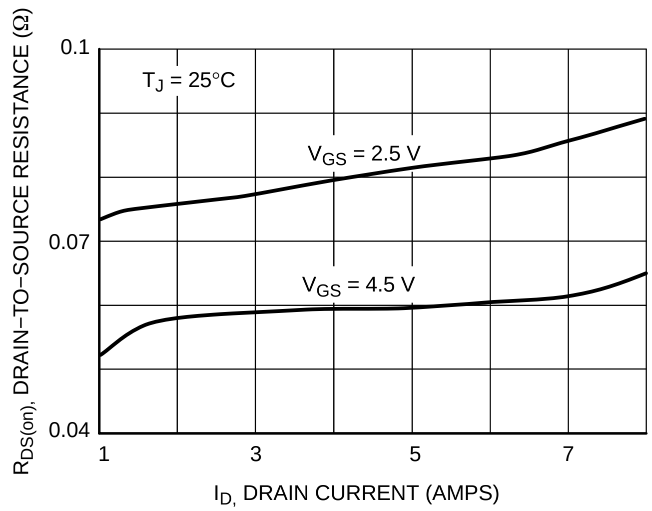


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

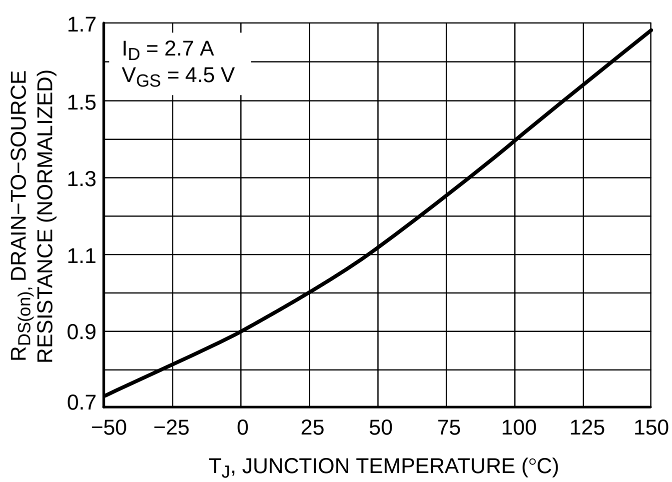


Figure 5. On−Resistance Variation with Temperature

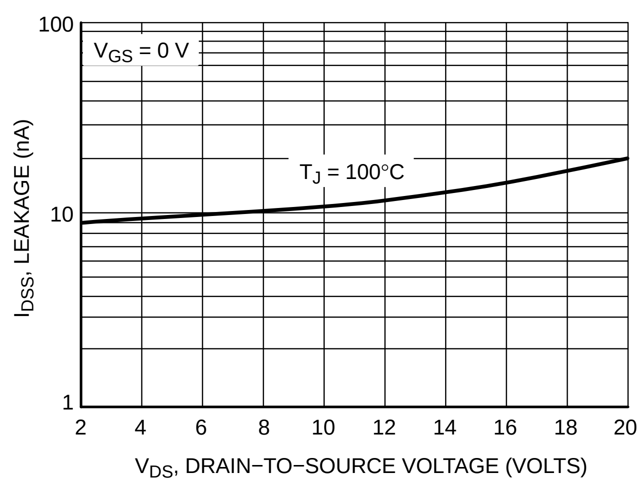


Figure 6. Drain−to−Source Leakage Current vs. Voltage

TYPICAL N−CHANNEL PERFORMANCE CURVES

(T_J = 25°C unless otherwise noted)

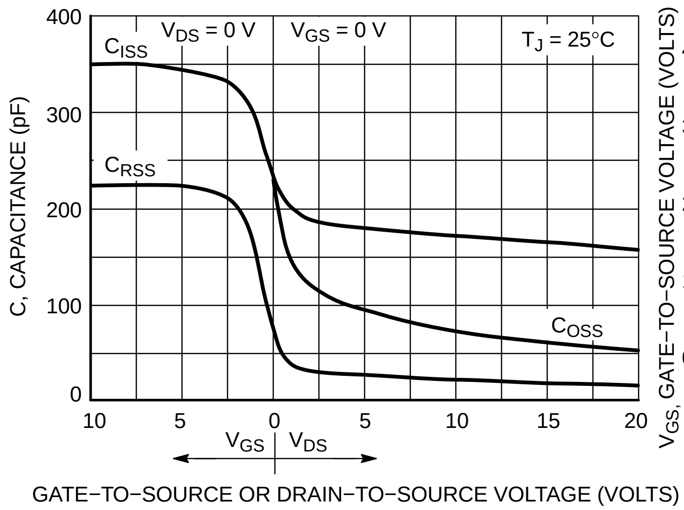


Figure 7. Capacitance Variation

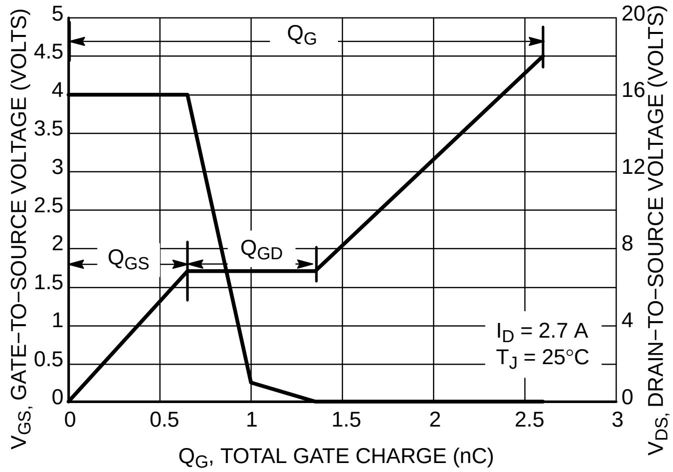


Figure 8. Gate−to−Source and Drain−to−Source Voltage vs. Total Charge

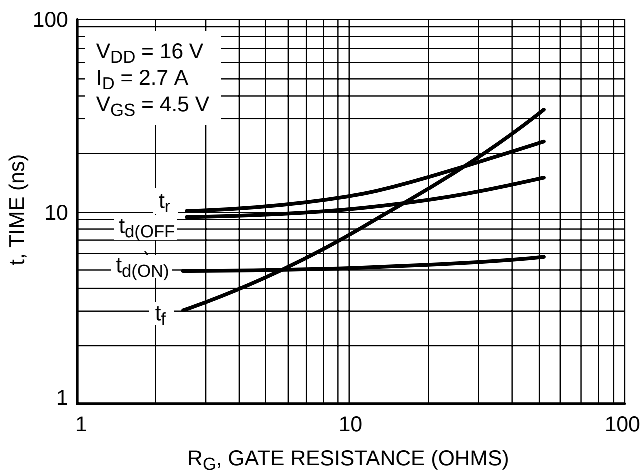


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

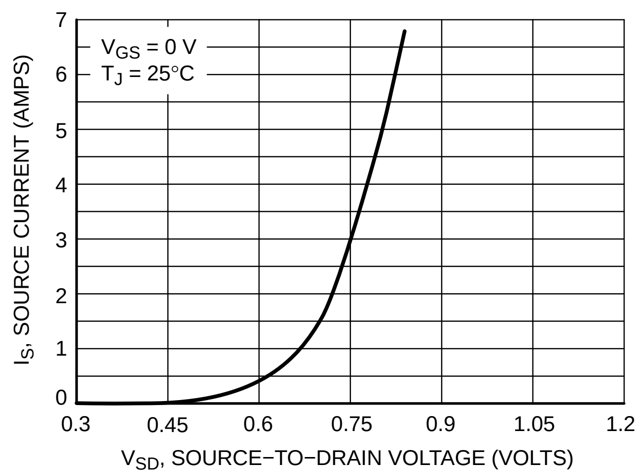


Figure 10. Diode Forward Voltage vs. Current

TYPICAL P−CHANNEL PERFORMANCE CURVES

(T_J = 25°C unless otherwise noted)

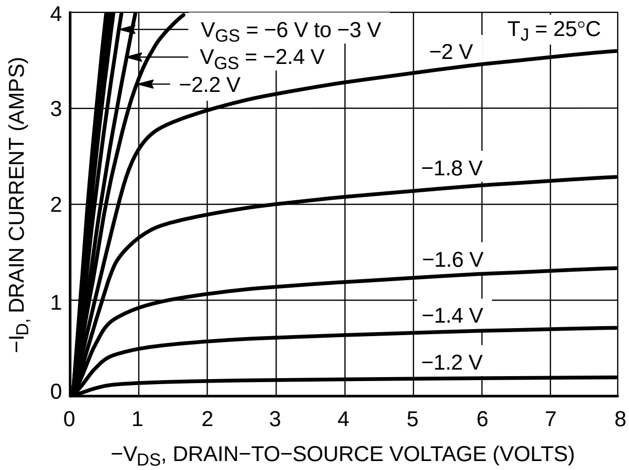


Figure 11. On−Region Characteristics

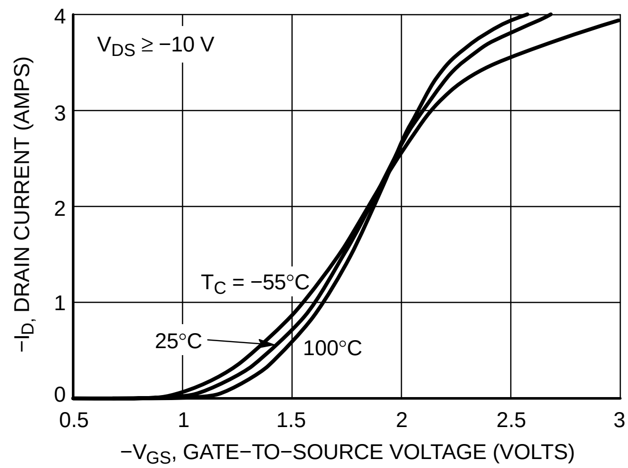


Figure 12. Transfer Characteristics

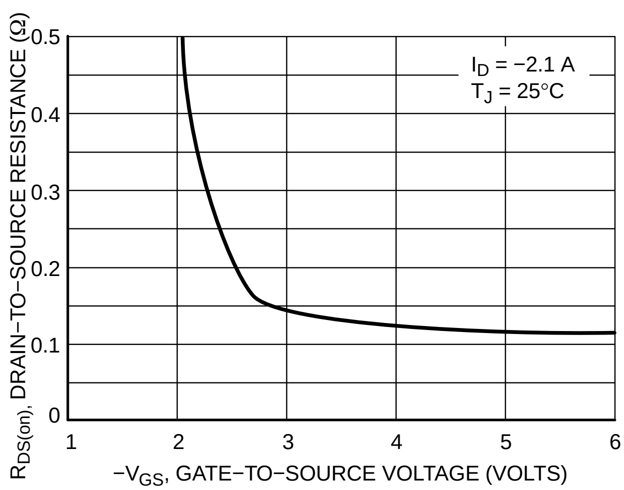


Figure 13. On−Resistance vs. Gate−to−Source Voltage

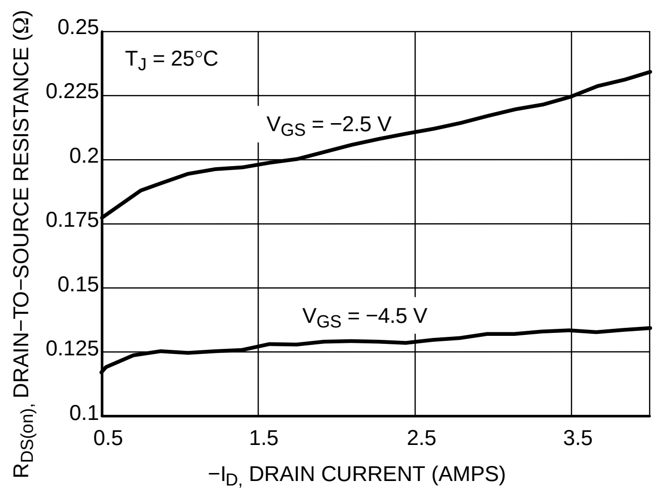


Figure 14. On−Resistance vs. Drain Current and Gate Voltage

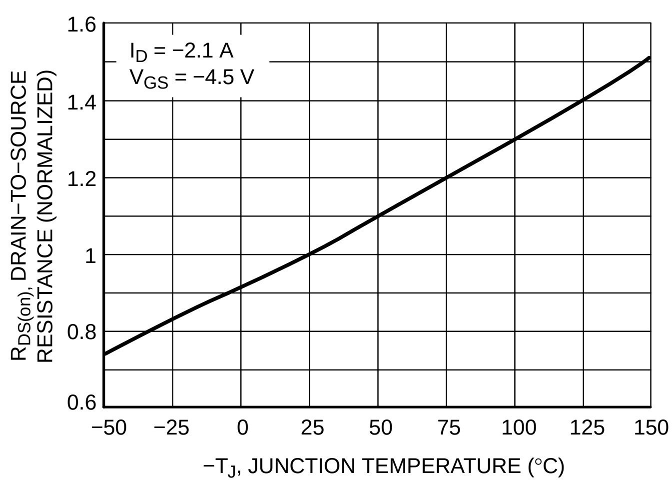


Figure 15. On−Resistance Variation with Temperature

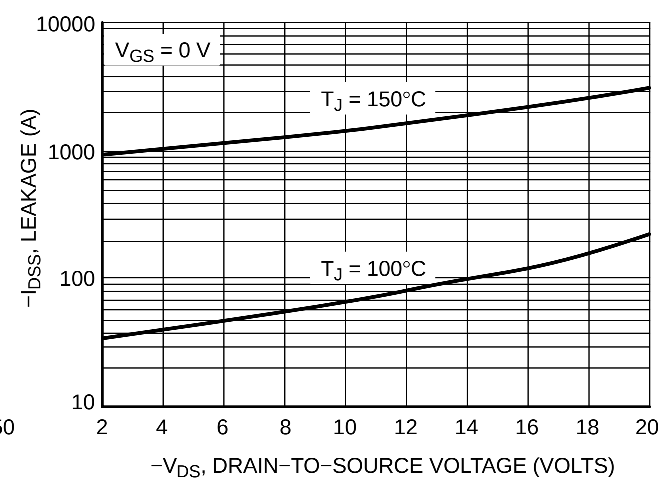


Figure 16. Drain−to−Source Leakage Current vs. Voltage

TYPICAL P−CHANNEL PERFORMANCE CURVES

(T_J = 25°C unless otherwise noted)

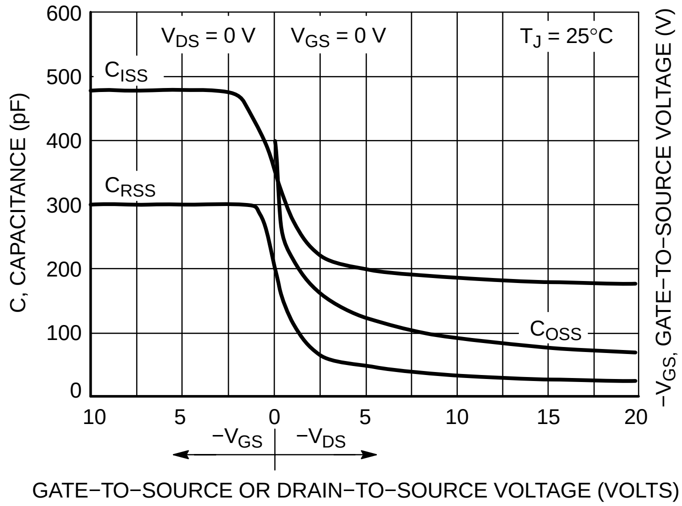


Figure 17. Capacitance Variation

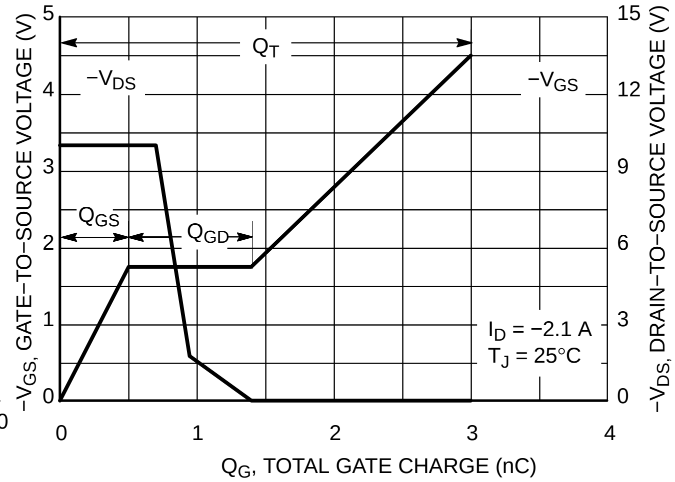


Figure 18. Gate−to−Source and Drain−to−Source Voltage vs. Total Charge

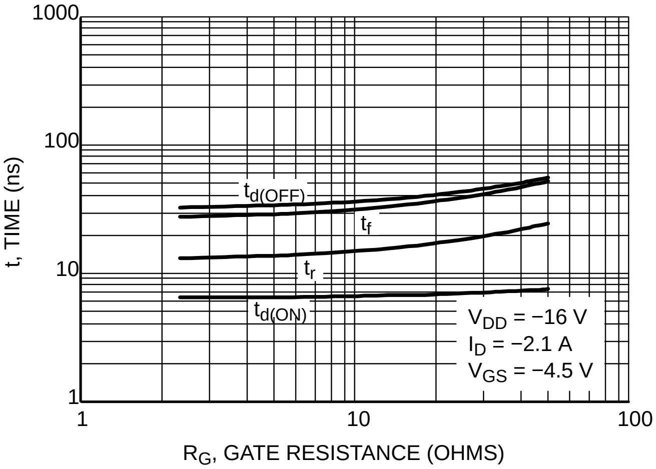


Figure 19. Resistive Switching Time Variation vs. Gate Resistance

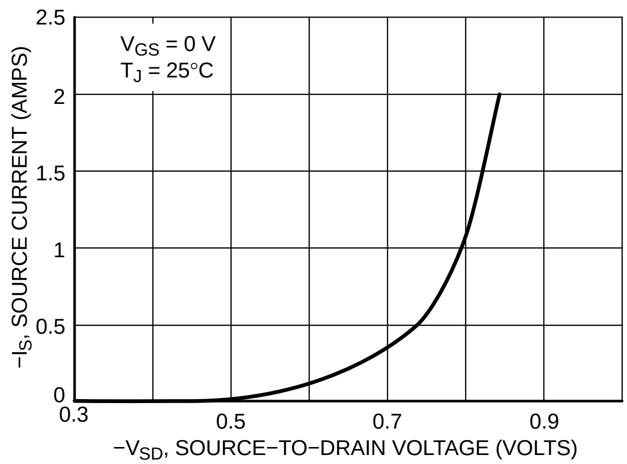


Figure 20. Diode Forward Voltage vs. Current

TYPICAL PERFORMANCE CURVES

(T_J = 25°C unless otherwise noted)

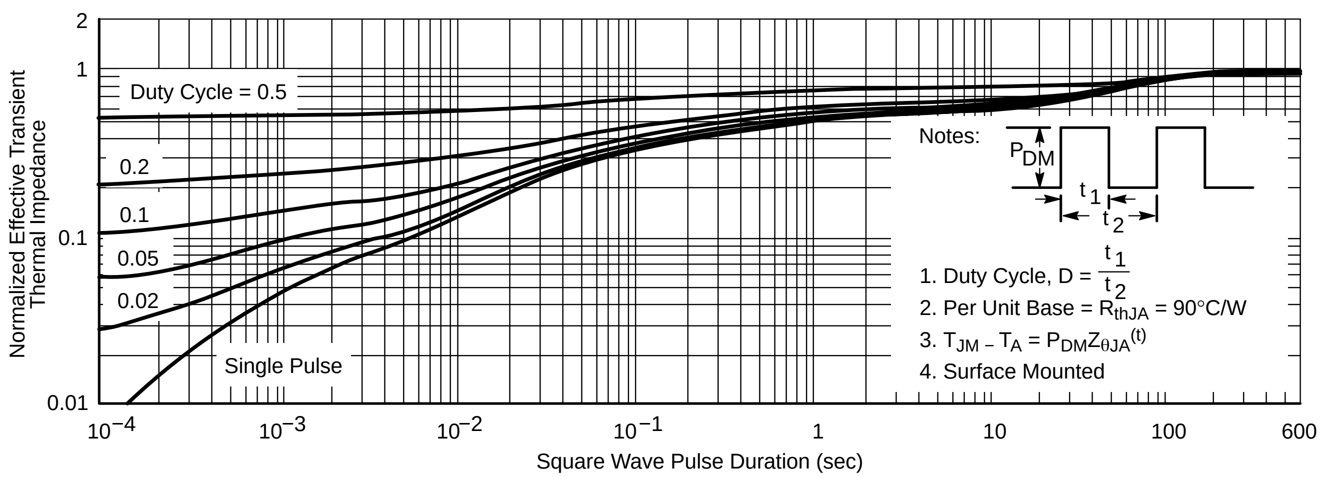


Figure 21. Thermal Response

SOLDERING FOOTPRINT*

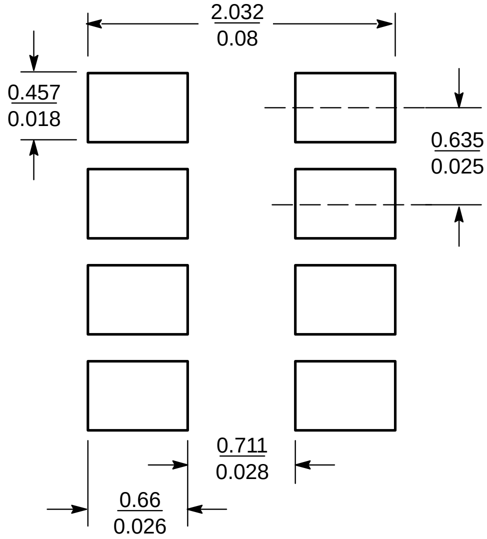


Figure 22. Basic

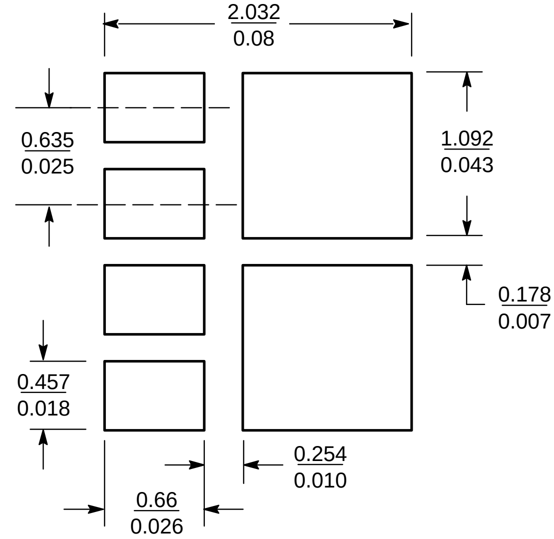


Figure 23. Style 2

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

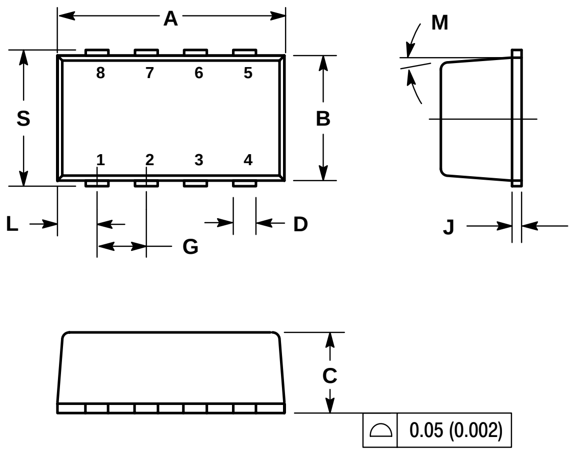
BASIC PAD PATTERNS

The basic pad layout with dimensions is shown in Figure 22. This is sufficient for low power dissipation MOSFET applications, but power semiconductor performance requires a greater copper pad area, particularly for the drain leads.

The minimum recommended pad pattern shown in Figure 23 improves the thermal area of the drain connections (pins 5, 6, 7, 8) while remaining within the confines of the basic footprint. The drain copper area is 0.0019 sq. in. (or 1.22 sq. mm). This will assist the power dissipation path away from the device (through the copper lead−frame) and into the board and exterior chassis (if applicable) for the single device. The addition of a further copper area and/or the addition of vias to other board layers will enhance the performance still further.

PACKAGE DIMENSIONS

ChipFET
CASE 1206A−03
ISSUE E



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MOLD GATE BURRS SHALL NOT EXCEED 0.13 MM PER SIDE.
4. LEADFRAME TO MOLDED BODY OFFSET IN HORIZONTAL AND VERTICAL SHALL NOT EXCEED 0.08 MM.
5. DIMENSIONS A AND B EXCLUSIVE OF MOLD GATE BURRS.
6. NO MOLD FLASH ALLOWED ON THE TOP AND BOTTOM LEAD SURFACE.
7. 1206A−01 AND 1206A−02 OBSOLETE. NEW STANDARD IS 1206A−03.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	2.95	3.10	0.116	0.122
B	1.55	1.70	0.061	0.067
C	1.00	1.10	0.039	0.043
D	0.25	0.35	0.010	0.014
G	0.65 BSC		0.025 BSC	
J	0.10	0.20	0.004	0.008
K	0.28	0.42	0.011	0.017
L	0.55 BSC		0.022 BSC	
M	5 ° NOM		5 ° NOM	
S	1.80	2.00	0.072	0.080

STYLE 2:
PIN 1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN 1
8. DRAIN 1

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PUBLICATION ORDERING INFORMATION

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